

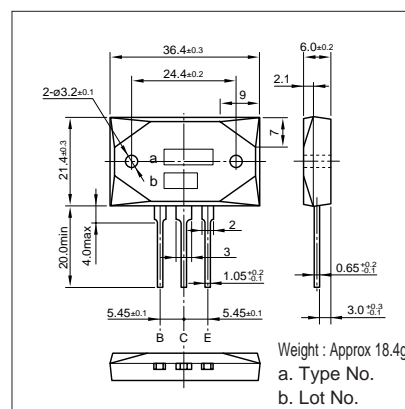
**Application :** Audio and General Purpose

( $T_a=25^{\circ}\text{C}$ )

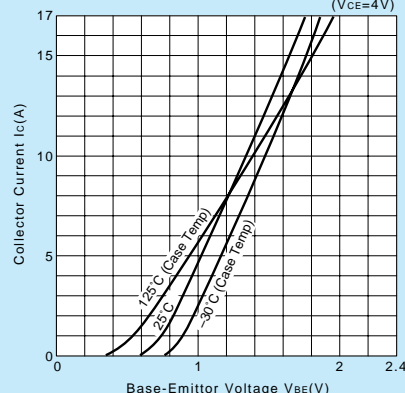
Symbol	Conditions	2SC2922	Unit
ICBO	V <sub>CB</sub> =180V	100max	μA
IEBO	V <sub>EB</sub> =5V	100max	μA
V(BR)CEO	I <sub>C</sub> =25mA	180min	V
hFE	V <sub>CE</sub> =4V, I <sub>C</sub> =8V	30min*	
VCE(sat)	I <sub>C</sub> =8A, I <sub>B</sub> =0.8A	2.0max	V
f <sub>T</sub>	V <sub>CE</sub> =12V, I <sub>E</sub> =-2A	50typ	MHz
COB	V <sub>CB</sub> =10V, f=1MHz	250typ	pF

### ■ Typical Switching Characteristics (Common Emitter)

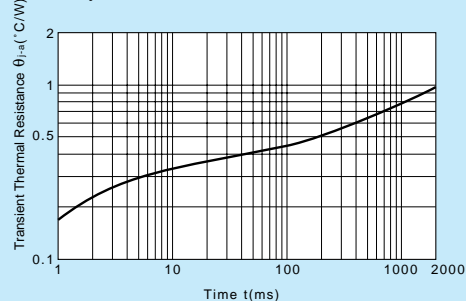
### External Dimensions MT-200



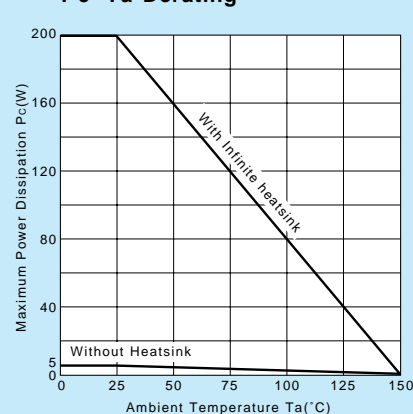
### **I<sub>C</sub>-V<sub>BE</sub> Temperature Characteristics (Typical)**



### $\theta_{j-a-t}$ Characteristics



## Pc-Ta Derating



Silicon PNP Epitaxial Planar Transistor (Complement to type 2SC2922)

Application : Audio and General Purpose

## ■ Absolute maximum ratings (Ta=25°C)

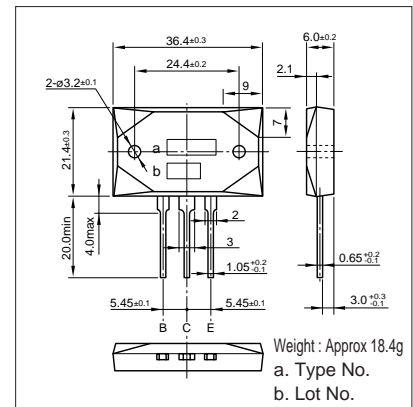
Symbol	2SA1216	Unit
VCBO	-180	V
VCEO	-180	V
VEBO	-5	V
IC	-17	A
IB	-5	A
PC	200(Tc=25°C)	W
TJ	150	°C
Tstg	-55 to +150	°C

## ■ Electrical Characteristics (Ta=25°C)

Symbol	Conditions	2SA1216	Unit
VCBO	VCB=-180V	-100max	μA
IEBO	VEB=-5V	-100max	μA
V(BR)CEO	IC=-25mA	-180min	V
hFE	VCE=-4V, IC=-8A	30min*	
VCE(sat)	IC=-8A, IB=-0.8A	-2.0max	V
fT	VCE=-12V, IE=2A	40typ	MHz
COB	VCB=-10V, f=1MHz	500typ	pF

\*hFE Rank O(30to60), Y(50to100), P(70to140), G(90to180)

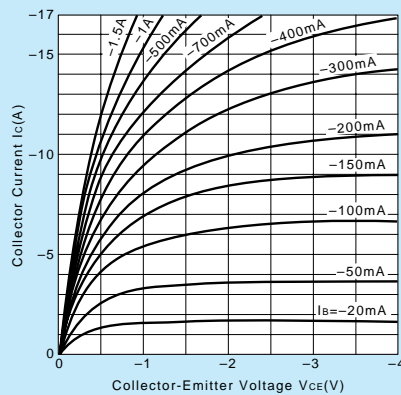
## External Dimensions MT-200



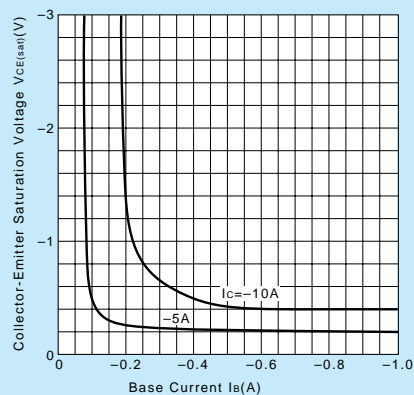
## ■ Typical Switching Characteristics (Common Emitter)

VCC (V)	RL (Ω)	IC (A)	VB2 (V)	IB1 (A)	IB2 (A)	ton (μs)	tstg (μs)	tf (μs)
-40	4	-10	5	-1	1	0.3typ	0.7typ	0.2typ

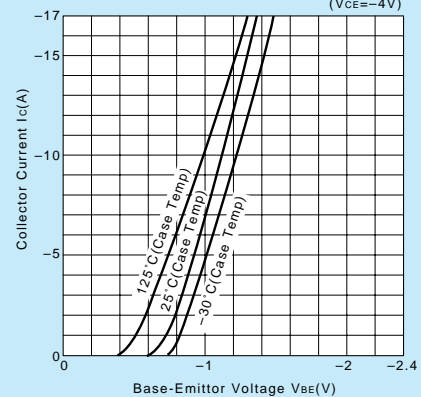
IC-VCE Characteristics (Typical)



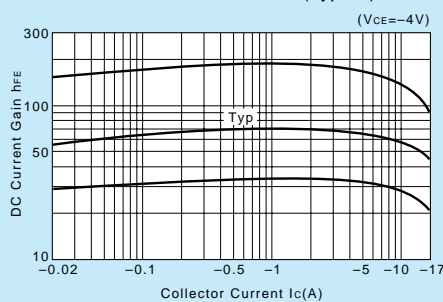
VCE(sat)-IB Characteristics (Typical)



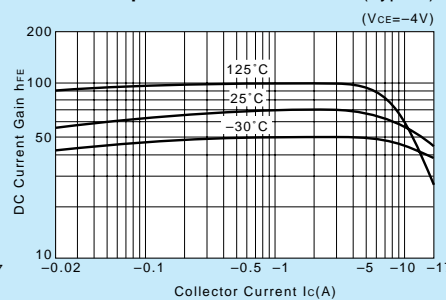
IC-VBE Temperature Characteristics (Typical)



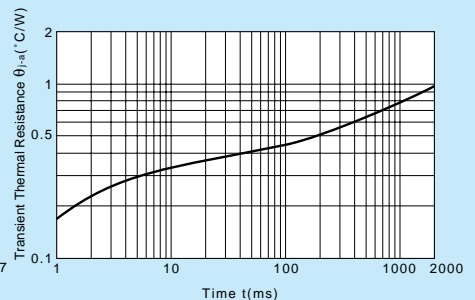
hFE-IC Characteristics (Typical)



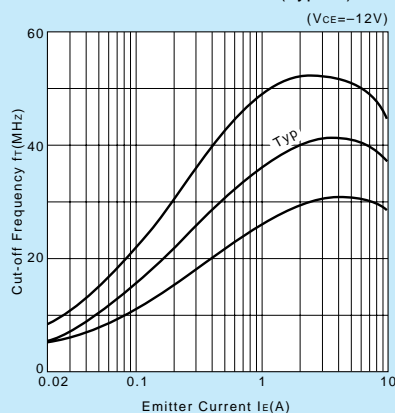
hFE-IC Temperature Characteristics (Typical)



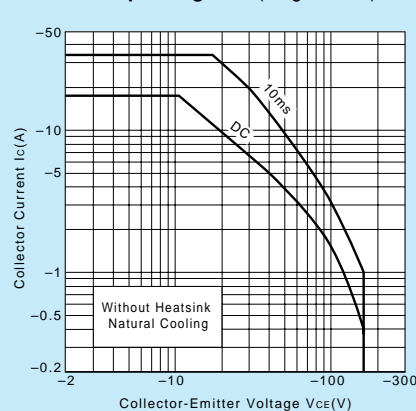
θJA-t Characteristics



fT-IE Characteristics (Typical)



Safe Operating Area (Single Pulse)



PC-Ta Derating

